





FPAB30BH60

Smart Power Module(SPM®) for Front-End Rectifier

General Description

FPAB30BH60 is an advanced smart power module(SPM®) of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is futher enhanced by the integrated under-voltage lock-out and over-current protection function.

Features

- Low thermal resistance due to Al₂O₃-DBC substrate
- 600V-30A 1-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- Typical switching frequency of 20kHz
- · Isolation rating of 2500Vrms/min.

Applications

• AC 85V ~ 264V single-phase front-end rectifier

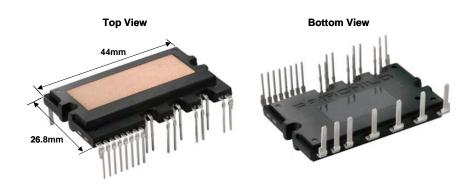


Fig. 1.

Integrated Power Functions

• PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration

Top View

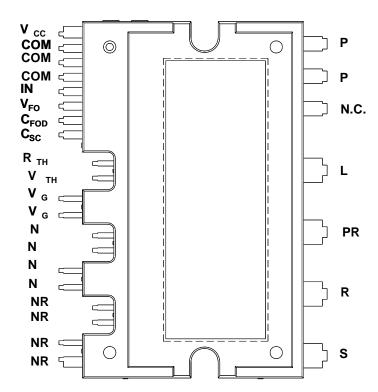


Fig. 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description		
1	V _{CC}	Common Bias Voltage for IC and IGBTs Driving		
2,3,4	COM	Common Supply Ground		
5	IN _(R)	Signal Input for Low-side R-phase IGBT		
6	V_{FO}	Fault Output		
7	C_{FOD}	Capacitor for Fault Output Duration Time Selection		
8	C _{SC}	Capacitor (Low-pass Filter) for Over Current Detection		
9	R _(TH)	NTC Thermistor terminal		
10	V _(TH)	NTC Thermistor terminal		
11,12	Vg	IGBT gate dummy		
13~16	N	IGBT emitter		
17~20	N _R	Negative DC-Link of Rectifier		
21,22	Р	Positive Rail of DC-Link		
23	N.C	No Connection		
24	L	Reactor connection pin		
25	P_{R}	Positive DC-Link of Rectifier		
26	R	AC input for R-phase		
27	S	AC input for S-phase		

Internal Equivalent Circuit and Input/Output Pins

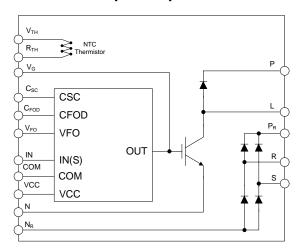


Fig. 3.

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FPAB30BH60	FPAB30BH60	SPM27-IA	-	-	10

Absolute Maximum Ratings ($T_J = 25$ °C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V _i	Applied between R-S	264	V_{RMS}
Supply Voltage (Surge)	V _{i(Surge)}	Applied between R-S	500	V
Output Voltage	V_{PN}	Applied between P- N	450	V
Output Voltage (Surge)	V _{PN(Surge)}	Applied between P- N	500	V
Collector-emitter Voltage	V _{CES}		600	V
Input Current (100% Load)	l _i	T _C < 95°C, V _i =220V, V _{PN} = 390V, V _{PWM} =20kHz	25	А
Input Current (125% Load)	I _{i(125%)}	T _C < 95°C, V _i =220V, V _{PN} = 390V, V _{PWM} =20kHz, 1min Non-repetitive	30	А
Collector Dissipation	P _C	T _C = 25°C per One IGBT	169	W
Operating Junction Temperature	TJ	(Note 1)	-20 ~ 150	°C

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V _{CC}	Applied between V _{CC} - COM	20	V
Input Signal Voltage	V _{IN}	Applied between IN - COM	-0.3~5.5	V
Fault Output Supply Voltage	V _{FO}	Applied between V _{FO} - COM	-0.3~V _{CC} +0.3	V
Fault Output Current	I _{FO}	Sink Current at V _{FO} Pin	5	mA
Current Sensing Input Voltage	V_{SC}	Applied between C _{SC} - COM	-0.3~V _{CC} +0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	T _C		-20 ~ 100	°C
Storage Temperature	T _{STG}		-40 ~ 125	°C
Isolation Voltage	V _{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V _{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to Case Thermal	$R_{\theta(j-c)Q}$	IGBT	-	-	0.74	°C/W
Resistance	$R_{\theta(j-c)F}$	FRD	-	-	1.44	°C/W
(Referenced to PKG center)	$R_{\theta(i-c)R}$	Rectifier	-	-	2.07	°C/W

2. For the measurement point of case temperature($T_{\mbox{\scriptsize C}}$), please refer to Fig. 2.

Note 1. The maximum junction temperature rating of the power chips integrated within the SPM® is 150 °C(@T_C \leq 100°C). However, to insure safe operation of the SPM®, the average junction temperature should be limited to T_{J(ave)} \leq 125°C (@T_C \leq 100°C)

Electrical Characteristics ($T_J = 25$ °C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
IGBT saturation voltage	V _{CE(sat)}	$V_{CC} = 15V, V_{IN} = 5V; I_{C} = 30A$	-	2.0	2.8	V
FRD forward voltage	V _{FF}	I _F = 30A	-	1.8	2.5	V
Rectifier forward voltage	V_{FR}	I _F = 30A	-	1.2	1.5	V
Switching Times	t _{ON}	$V_{PN} = 400V, V_{CC} = 15V, I_{C} = 30A$	-	650	-	ns
	t _{C(ON)}	V _{IN} = 0V ↔ 5V, Inductive Load	-	400	-	ns
	t _{OFF}	(Note 3)	-	620	-	ns
	t _{C(OFF)}	(1000 0)	-	200	-	ns
	t _{rr}		-	60	-	ns
	I _{rr}		-	3.5	-	Α
Collector - emitter Leakage Current	I _{CES}	$V_{CE} = V_{CES}$	-	-	250	μА

Control Part

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Quiescent V _{CC} Supply Current	I _{QCCL}	$V_{CC} = 15V$, $IN = 0V$ $V_{CC} - COM$	-	-	26	mA
Fault Output Voltage	V_{FOH}	V_{SC} = 0V, V_{FO} Circuit: 4.7k Ω to 5V Pull-up	4.5	-	-	V
	V_{FOL}	V_{SC} = 1V, V_{FO} Circuit: 4.7k Ω to 5V Pull-up	-	-	0.8	V
Over Current Trip Level	V _{SC(ref)}	V _{CC} = 15V	0.45	0.5	0.55	V
Supply Circuit Under-	UV _{CCD}	Detection Level	10.7	11.9	13.0	V
Voltage Protection	UV _{CCR}	Reset Level	11.2	12.4	13.2	V
Fault-out Pulse Width	t _{FOD}	C _{FOD} = 33nF (Note 4)	1.4	1.8	2.0	ms
ON Threshold Voltage	V _{IN(ON)}	Applied between IN - COM	3.0	-	-	V
OFF Threshold Voltage	V _{IN(OFF)}		-	-	0.8	V
Resistance of Thermistor	R _{TH}	@ T _C = 25°C (Note Fig. 9)	-	50	-	kΩ
		@ T _C = 100°C (Note Fig. 9)	-	2.99	-	kΩ

Note
 t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. t_{C(ON)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Note
4. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

Electrical Characteristics

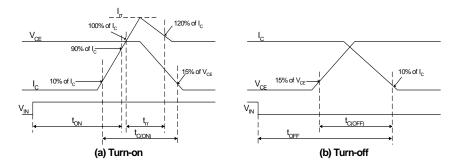


Fig. 4. Switching Time Definition

Mechanical Characteristics and Ratings

Item		Condition			Limits		
nem		ondition	Min.	Тур.	Max.	Units	
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N•m	
Device Flatness	Note Fig. 5		0	-	+120	μm	
Weight			-	15.00	-	g	

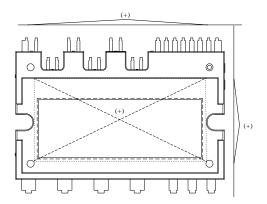
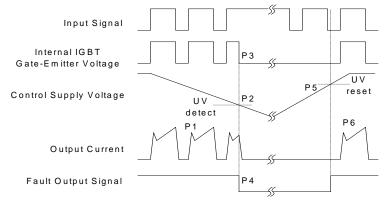


Fig. 5. Flatness Measurement Position

Time Charts of SPMs Protective Function

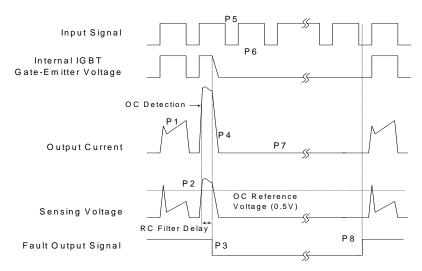


P1: Normal operation - IGBT ON and conducting current

P2 : Under voltage detection P3 : IGBT gate interrupt P4 : Fault signal generation P5 : Under voltage reset

P6: Normal operation - IGBT ON and conducting current

Fig. 6. Under-Voltage Protection



P1: Normal operation - IGBT ON and conducting current

P2 : Over current detection

P3: IGBT gate interrupt / Fault signal generation

P4: IGBT is slowly turned off

P5 : IGBT OFF signal

P6: IGBT ON signal - but IGBT cannot be turned on during the fault Output activation

P7: IGBT OFF state

P8: Fault Output reset and normal operation start

Fig. 7. Over Current Protection

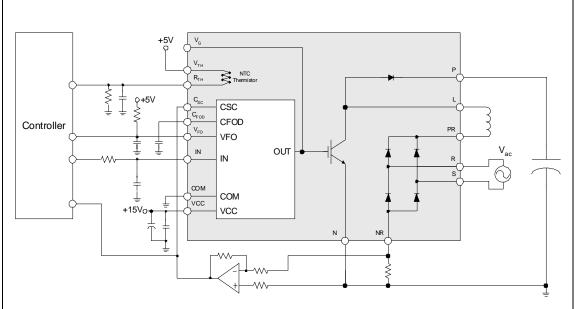


Fig. 8. Application Example

R-T Graph

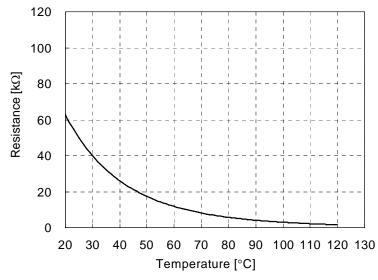
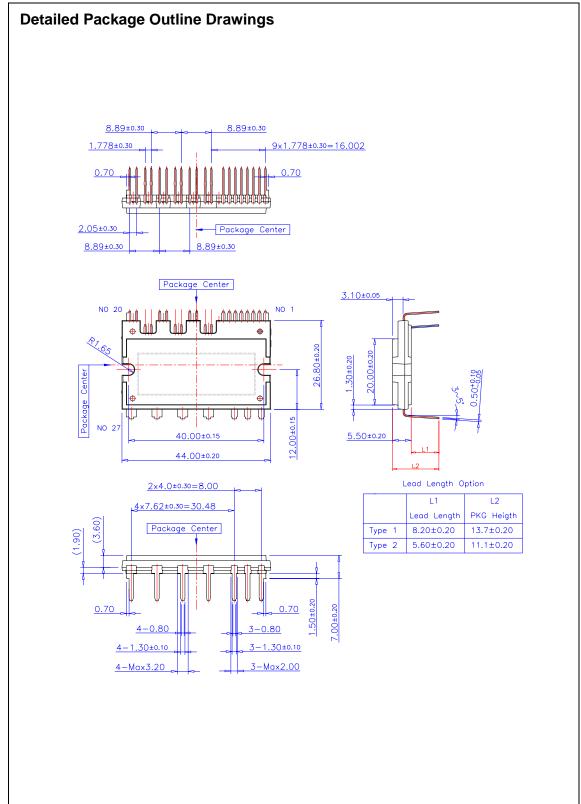
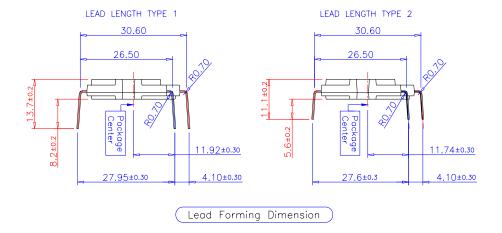
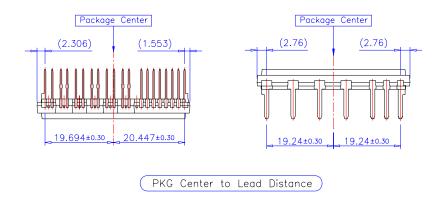


Fig. 9. R-T Curve of the Built-in Thermistor

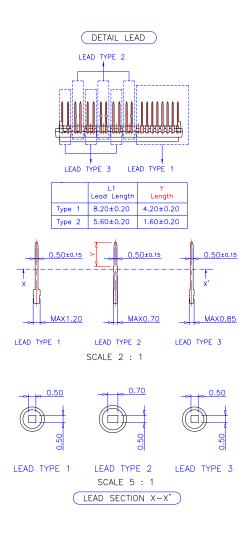


Detailed Package Outline Drawings





Detailed Package Outline Drawings







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Rev. I29